Panasonic

XN01110G

Silicon PNP epitaxial planar type

For switching/digital circuits

Features

- Two elements incorporated into one package (Emitter-coupled transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

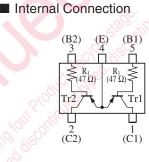
Basic Part Number

• UNR2110 \times 2

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-50	V	
Collector-emitter voltage (Base open)	V _{CEO}	-50	V	
Collector current	I _C	-100	mA	
Total power dissipation	P _T	300	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

- Package
- Code Mini5-G2
- Pin Name
 1: Collector (Tr1) 4:
 - tor (Tr1) 4: Emitter tor (Tr2) 5: Base (Tr1)
- 2: Collector (Tr2) 3: Base (Tr2)
- Marking Symbol: AD



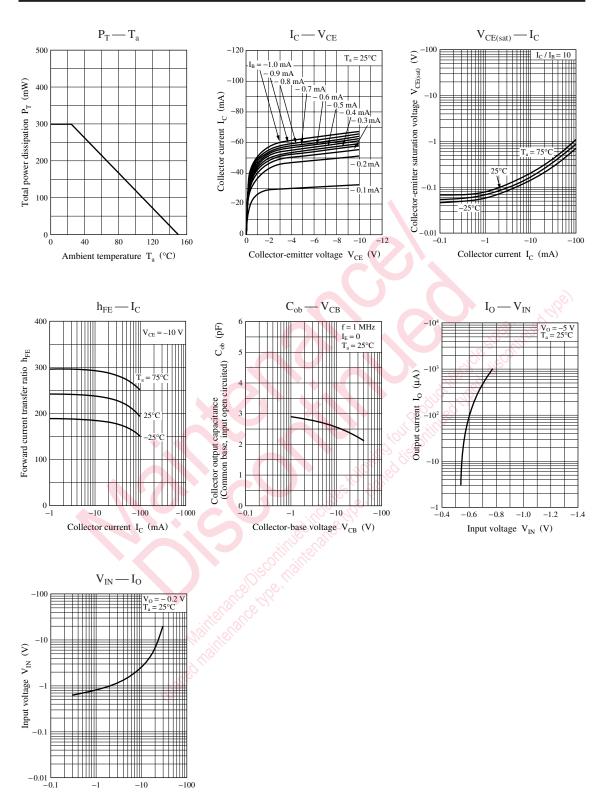
Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu A, \ I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 {\rm mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = -50 \text{ V}, I_B = 0$			- 0.5	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = -6 V, I_C = 0$			- 0.01	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	160		460	
h _{FE} Ratio *	h _{FE(Small}	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	0.50	0.99		
- NOT	/Large)					
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.3 \text{ mA}$			- 0.25	V
Output voltage high-level	V _{OH}	$V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	V _{OL}	$V_{CC} = -5 \text{ V}, \text{ V}_{B} = -2.5 \text{ V}, \text{ R}_{L} = 1 \text{ k}\Omega$			- 0.2	V
Input resistance	R ₁		-30%	47	+30%	kΩ
Transition frequency	f _T	$V_{CB} = -10$ V, $I_E = 1$ mA, $f = 200$ MHz		80		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Ratio between 2 elements

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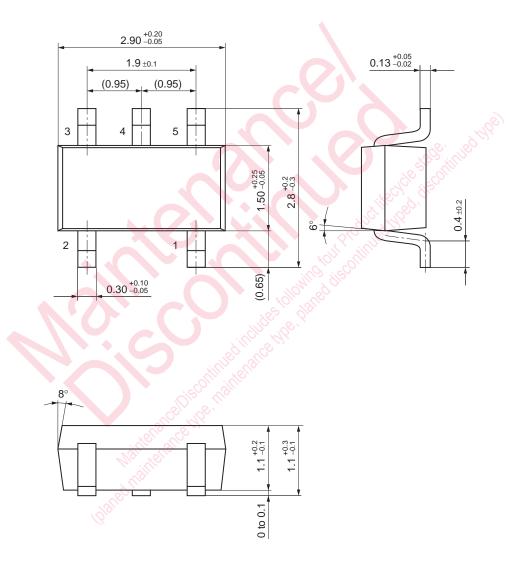


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Panasonic

Mini5-G2

Unit: mm



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